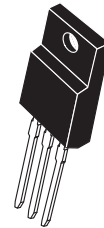




BMS3004

P-Channel Power MOSFET -75V, -68A, 8.5mΩ, TO-220F-3SG

ON Semiconductor®

<http://onsemi.com>

TO-220F-3SG

Features

- ON-resistance $R_{DS(on)1}=6.5\text{m}\Omega$ (typ.)
- Input capacitance $C_{iss}=13400\text{pF}$ (typ.)
- 4V drive

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	V_{DSS}		-75	V
Gate to Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		-68	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	-272	A
Allowable Power Dissipation	P_D		2.0	W
		$T_c=25^\circ\text{C}$	40	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$
Avalanche Energy (Single Pulse) *1	E_{AS}		380	mJ
Avalanche Current *2	I_{AV}		-54	A

Note : *1 $V_{DD}=-48\text{V}$, $L=100\mu\text{H}$, $I_{AV}=-54\text{A}$ (Fig.1)*2 $L \leq 100\mu\text{H}$, Single pulse

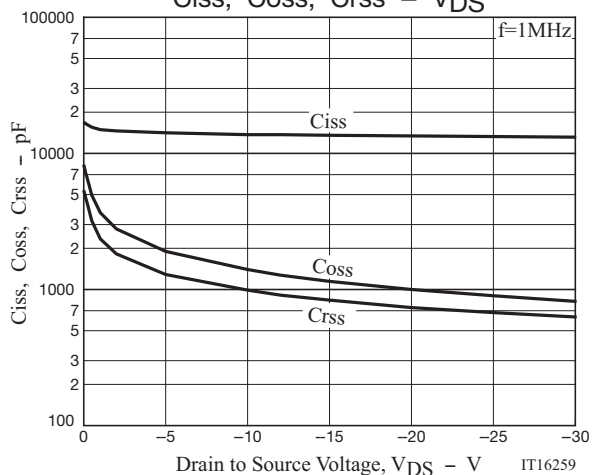
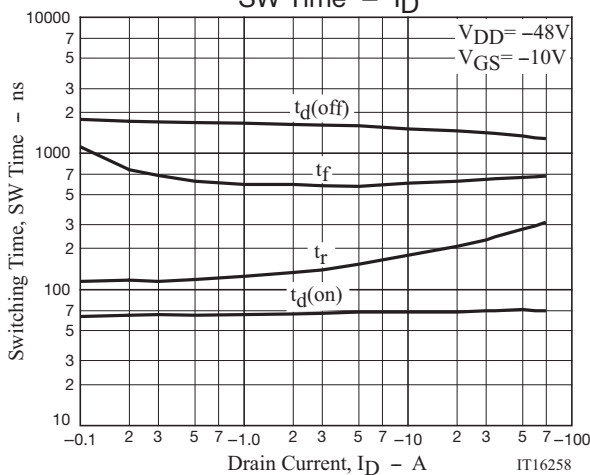
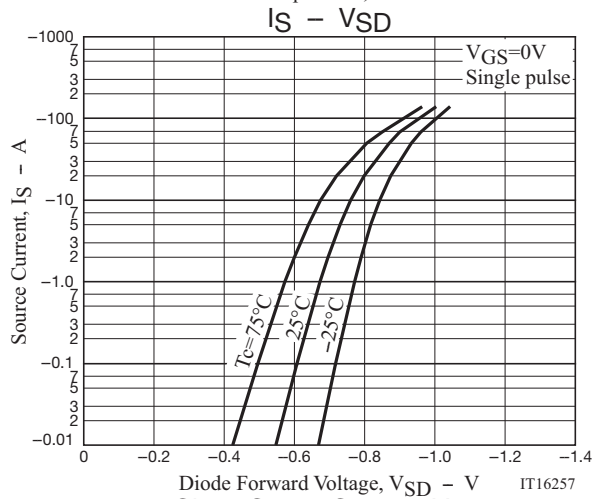
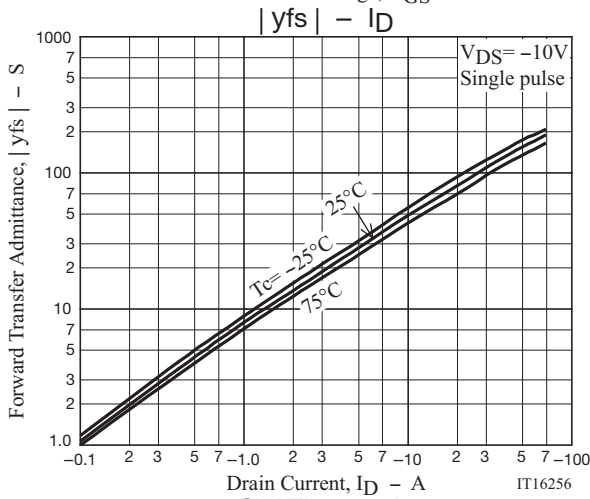
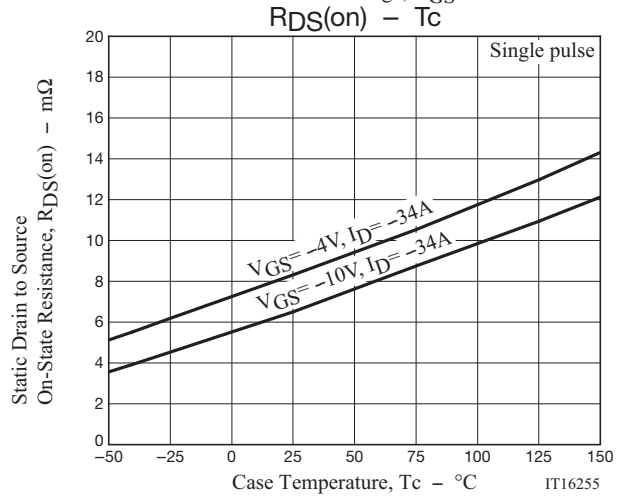
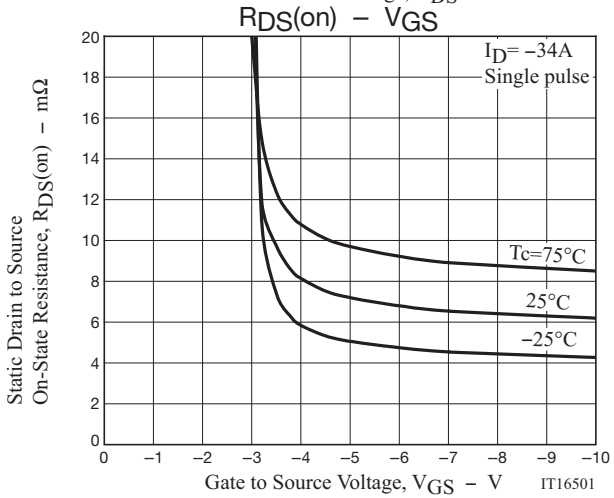
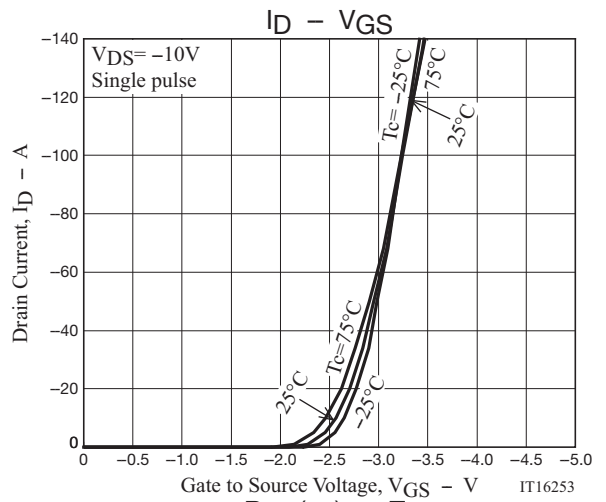
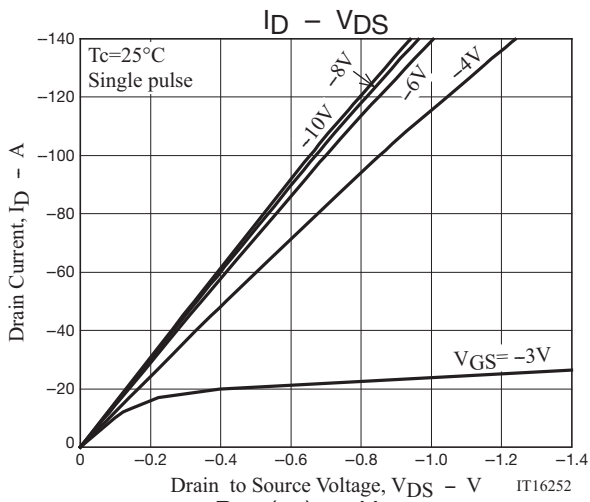
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1\text{mA}$, $V_{GS}=0\text{V}$	-75			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-75\text{V}$, $V_{GS}=0\text{V}$			-10	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16\text{V}$, $V_{DS}=0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10\text{V}$, $I_D=-1\text{mA}$	-1.2		-2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10\text{V}$, $I_D=-34\text{A}$		120		S
Static Drain to Source On-State Resistance	$R_{DS(on)1}$	$I_D=-34\text{A}$, $V_{GS}=-10\text{V}$		6.5	8.5	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D=-34\text{A}$, $V_{GS}=-4\text{V}$		8.3	11.4	$\text{m}\Omega$
Input Capacitance	C_{iss}			13400		pF
Output Capacitance	C_{oss}	$V_{DS}=-20\text{V}$, $f=1\text{MHz}$		1000		pF
Reverse Transfer Capacitance	C_{rss}			740		pF
Turn-ON Delay Time	$t_{d(on)}$	See Fig.2		70		ns
Rise Time	t_r			245		ns
Turn-OFF Delay Time	$t_{d(off)}$			1400		ns
Fall Time	t_f			650		ns
Total Gate Charge	Q_g				300	
Gate to Source Charge	Q_{gs}	$V_{DS}=-48\text{V}$, $V_{GS}=-10\text{V}$, $I_D=-68\text{A}$		30		nC
Gate to Drain "Miller" Charge	Q_{gd}			70		nC
Diode Forward Voltage	V_{SD}	$I_S=-68\text{A}$, $V_{GS}=0\text{V}$		-0.9	-1.5	V
Reverse Recovery Time	t_{rr}	See Fig.3		146		ns
Reverse Recovery Charge	Q_{rr}	$I_S=-68\text{A}$, $V_{GS}=0\text{V}$, $di/dt=-100\text{A}/\mu\text{s}$		470		nC

ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.



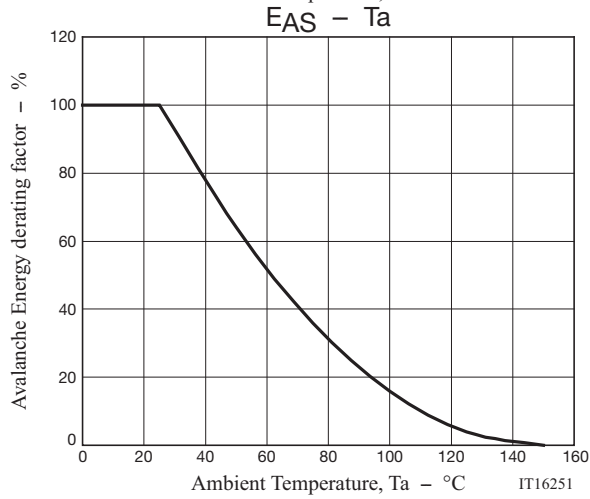
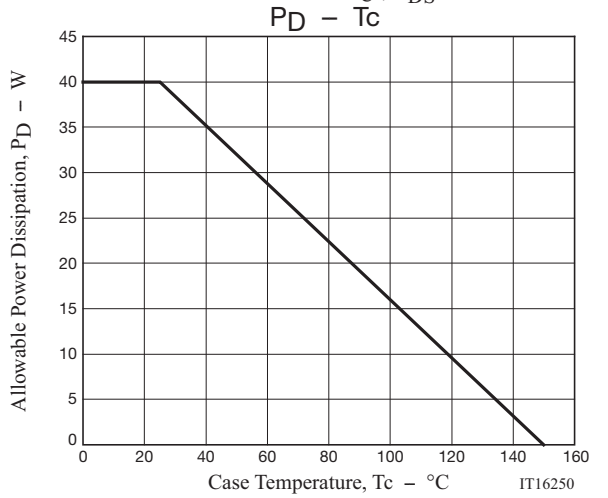
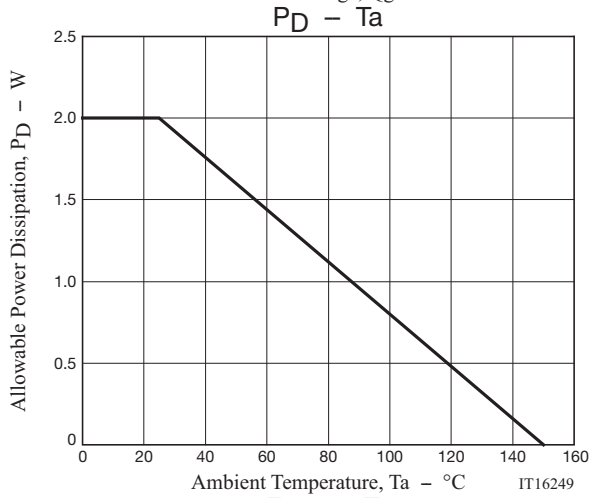
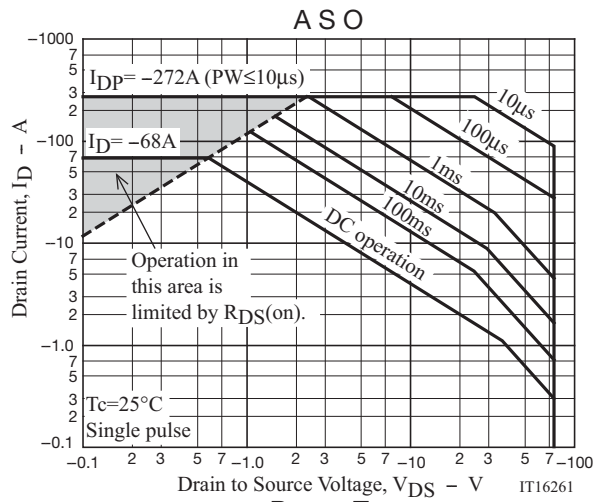
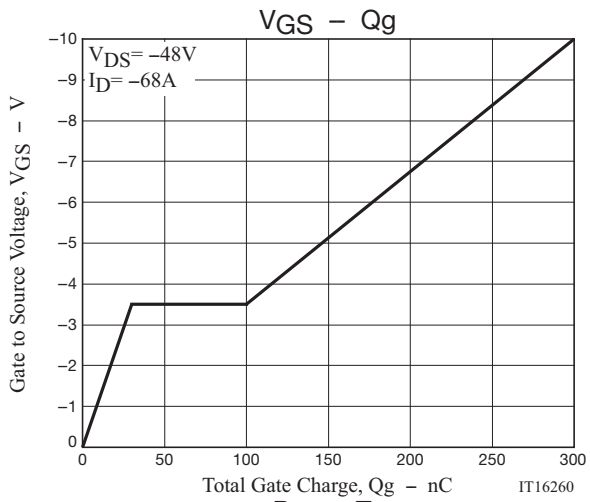


Fig.1 Unclamped Inductive Switching Test Circuit

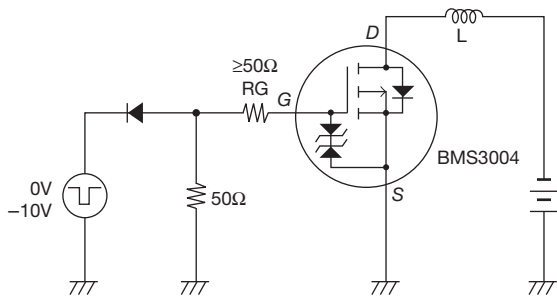


Fig.2 Switching Time Test Circuit

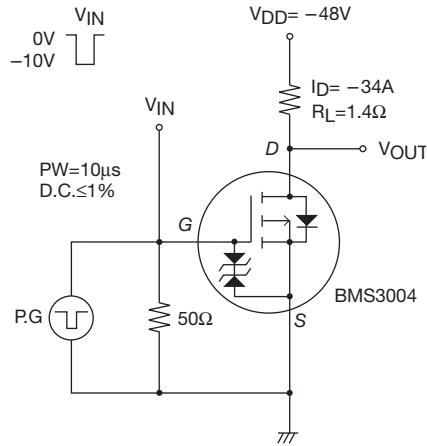
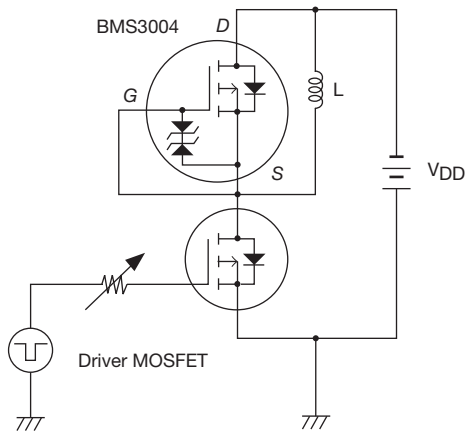


Fig.3 Reverse Recovery Time Test Circuit



Note on usage : Since the BMS3004 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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